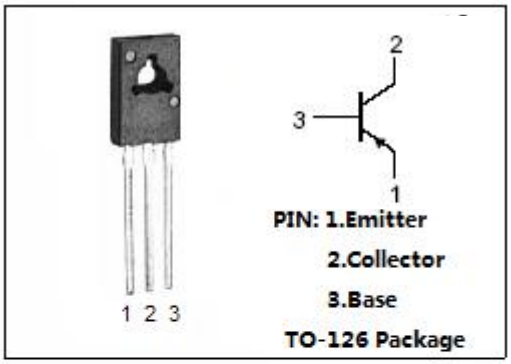
isc Silicon PNP Power Transistor 2SA1120

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -20V (Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$ = -1.0V(Max.)@ I_C= 0.1A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

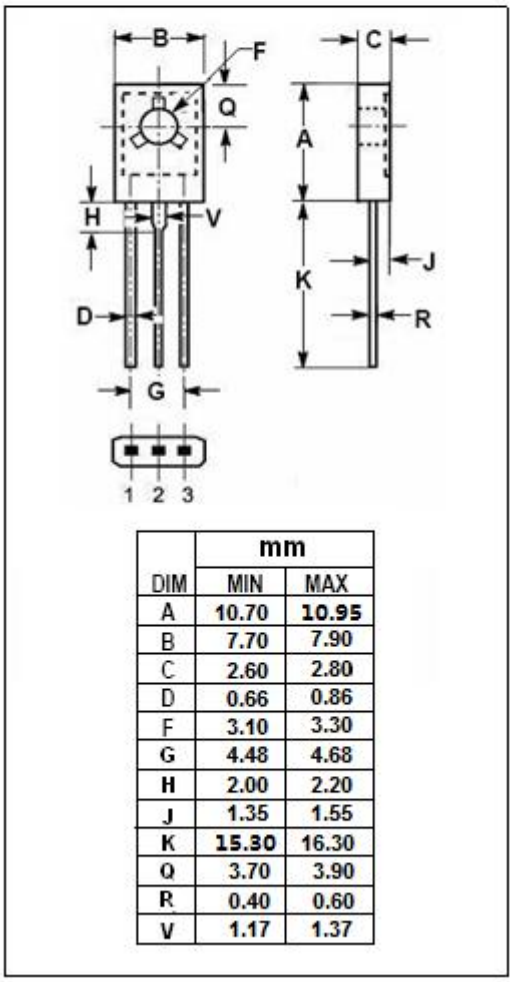
APPLICATIONS

- Strobo flash applications
- Audio power amplifer applications



ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-5	A
I_{CM}	Collector Current-Peak	-8	A
I_E	Emitter Current-Continuous	5	A
I_{EM}	Emitter Current-Peak	8	A
P_C	Collector Power Dissipation @T_a=25℃	1.0	W
	Collector Power Dissipation @T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-20			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-8			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.1A			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -4A; V_{CE}= -2V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -35V; I_E= 0			-100	nA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -8V; I_C=0			-100	nA
h_{FE-1}	DC Current Gain	I_C= -0.5A; V_{CE}= -2V	100		320	
h_{FE-2}	DC Current Gain	I_C= -4A; V_{CE}= -2V	70			

◆ **h_{FE-1} Classifications**

O	Y
100-200	160-320